

SN74HCS126 3 ステート出力およびシュミット・トリガ入力搭載、クワッド・バッファ

1 特長

- 広い動作電圧範囲: 2V~6V
- シュミット・トリガ入力により低速の信号またはノイズの多い信号に対応
- 低消費電力
 - I_{CC} : 100nA (標準値)
 - 入力リーク電流: ± 100 nA (標準値)
- 6V で ± 7.8 mA の出力駆動能力
- 広い周囲温度範囲: $-40^{\circ}\text{C} \sim +125^{\circ}\text{C}$, T_A

2 アプリケーション

- デジタル信号のイネーブルまたはディスエーブル
- インジケータ LED の制御
- スイッチのデバウンス
- 低速またはノイズの多い入力信号の除去

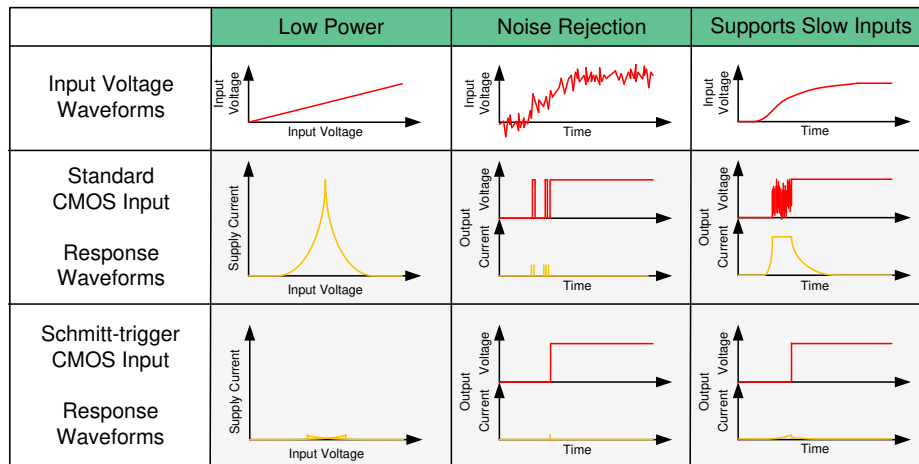
3 概要

このデバイスは、3 ステート出力とシュミット・トリガ入力を備えた 4 個の独立なバッファを搭載しています。各ゲートはブール関数 $Y = A$ を正論理で実行します。OE ピンに Low を印加することで、出力をハイ・インピーダンス状態にできます。

パッケージ情報

部品番号	パッケージ (1)	本体サイズ (公称)
SN74HCS126PW	TSSOP (14)	5.00mm × 4.40mm
SN74HCS126D	SOIC (14)	9.90mm × 3.90mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



シュミット・トリガ入力の利点



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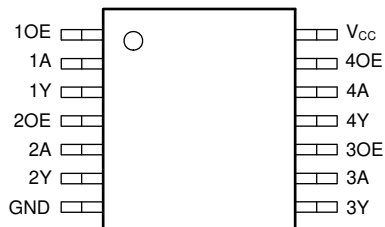
4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision A (March 2021) to Revision B (May 2023)	Page
• 「パッケージ情報」表のピン数を 16 から 14 に更新	1

Changes from Revision * (June 2020) to Revision A (March 2021)	Page
• Changed the unit of I_L from μA to nA.....	5

5 Pin Configuration and Functions



✎ 5-1. PW or D Package 14-Pin TSSOP or SOIC Top View

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1OE	1	Input	Channel 1, Output Enable, Active High
1A	2	Input	Channel 1, Input A
1Y	3	Output	Channel 1, Output Y
2OE	4	Input	Channel 2, Output Enable, Active High
2A	5	Input	Channel 2, Input A
2Y	6	Output	Channel 2, Output Y
GND	7	—	Ground
3Y	8	Output	Channel 3, Output Y
3A	9	Input	Channel 3, Input A
3OE	10	Input	Channel 3, Output Enable, Active High
4Y	11	Output	Channel 4, Output Y
4A	12	Input	Channel 4, Input A
4OE	13	Input	Channel 4, Output Enable, Active High
V _{CC}	14	—	Positive Supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V_{CC}	Supply voltage	−0.5	7	V
I_{IK}	Input clamp current ⁽²⁾	$V_I < 0$ or $V_I > V_{CC}$	±20	mA
I_{OK}	Output clamp current ⁽²⁾	$V_O < 0$ or $V_O > V_{CC}$	±20	mA
I_O	Continuous output current	$V_O = 0$ to V_{CC}	±35	mA
I_{CC}	Continuous current through V_{CC} or GND		±70	mA
T_J	Junction temperature		150	°C
T_{stg}	Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 2	±4000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1500	

- (1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	2	5	6	V
V_I	Input voltage	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	V
T_A	Ambient temperature	−40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74HCS126		UNIT
		D (SOIC)	PW (TSSOP)	
		14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	133.6	151.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	89	79.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	89.5	94.7	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	45.5	25.2	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	89.1	94.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V _{CC}	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{T+}	Positive switching threshold			2 V	0.7		1.5	V
				4.5 V	1.7		3.15	
				6 V	2.1		4.2	
V _{T-}	Negative switching threshold			2 V	0.3		1	V
				4.5 V	0.9		2.2	
				6 V	1.2		3	
ΔV _T	Hysteresis (V _{T+} - V _{T-})			2 V	0.2		1	V
				4.5 V	0.4		1.4	
				6 V	0.6		1.6	
V _{OH}	High-level output voltage	V _I = V _{IH} or V _{IL}	I _{OH} = -20 μA	2 V to 6 V	V _{CC} - 0.1	V _{CC} - 0.002		V
			I _{OH} = -6 mA	4.5 V	4	4.3		
			I _{OH} = -7.8 mA	6 V	5.4	5.75		
V _{OL}	Low-level output voltage	V _I = V _{IH} or V _{IL}	I _{OL} = 20 μA	2 V to 6 V		0.002	0.1	V
			I _{OL} = 6 mA	4.5 V		0.18	0.3	
			I _{OL} = 7.8 mA	6 V		0.22	0.33	
I _I	Input leakage current	V _I = V _{CC} or 0		6 V		±100	±1000	nA
I _{OZ}	Off-state (high-impedance state) output current	V _O = V _{CC} or 0		6 V		0.01	2	μA
I _{CC}	Supply current	V _I = V _{CC} or 0, I _O = 0		6 V		0.1	2	μA
C _i	Input capacitance			2 V to 6 V			5	pF

(1) T_A = 25°C

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V _{CC}	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{pd}	Propagation delay	A	Y	2 V		15	50	ns
				4.5 V		8	30	
				6 V		7	26	
t _{en}	Enable time	OE	Y	2 V		18	36	ns
				4.5 V		9	14	
				6 V		7	12	
t _{dis}	Disable time	OE	Y	2 V		15	27	ns
				4.5 V		10	17	
				6 V		9	14	
t _t	Transition-time		Any	2 V		9	16	ns
				4.5 V		5	9	
				6 V		4	8	

(1) T_A = 25°C

6.7 Operating Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
C_{pd}	Power dissipation capacitance per gate	No load		10		pF

(1) $T_A = 25^\circ\text{C}$

6.8 Typical Characteristics

$T_A = 25^\circ\text{C}$

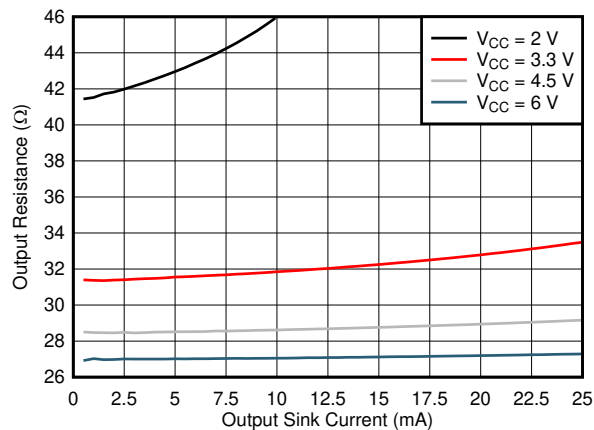


FIG 6-1. Output driver resistance in LOW state.

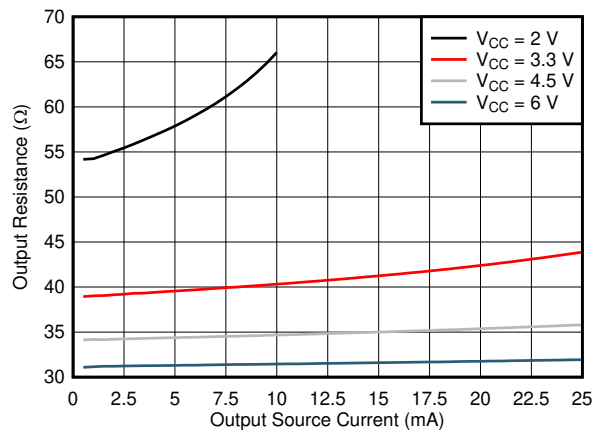


FIG 6-2. Output driver resistance in HIGH state.

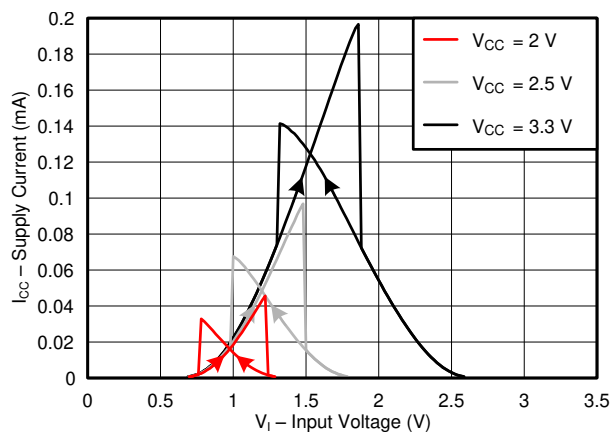


FIG 6-3. Supply current across input voltage, 2-, 2.5-, and 3.3-V supply

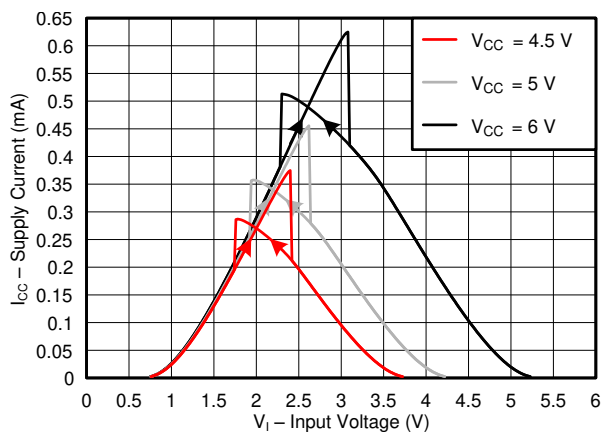


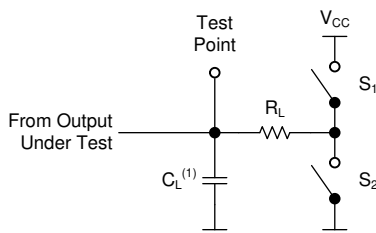
FIG 6-4. Supply current across input voltage, 4.5-, 5-, and 6-V supply

7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \Omega$, $t_t < 2.5 \text{ ns}$.

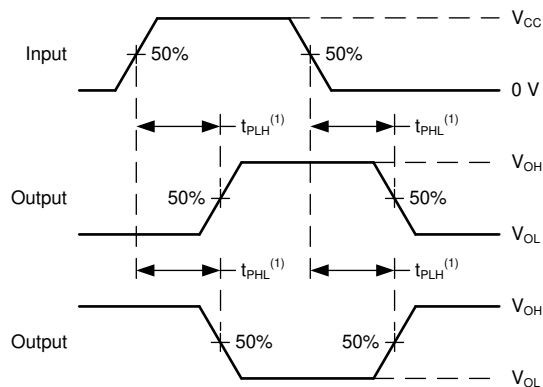
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



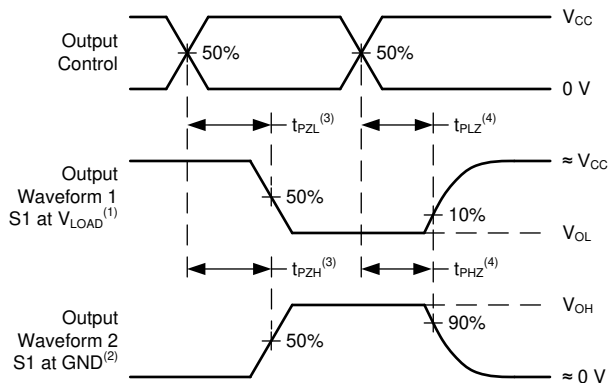
(1) C_L includes probe and test-fixture capacitance.

7-1. Load Circuit for 3-State Outputs

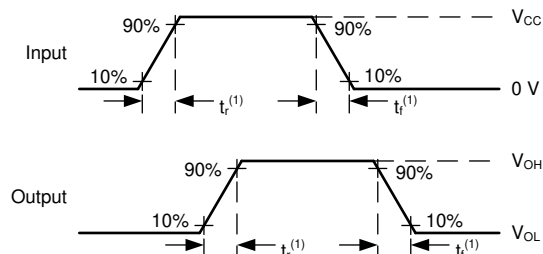


(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

7-2. Voltage Waveforms Propagation Delays



7-3. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t .

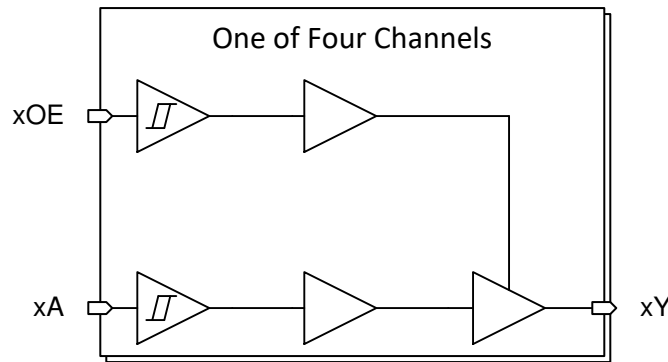
7-4. Voltage Waveforms, Input and Output Transition Times

8 Detailed Description

8.1 Overview

This device contains four independent buffer with 3-state outputs and Schmitt-trigger inputs. Each gate performs the Boolean function $Y = A$ in positive logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-State outputs. The three states that these outputs can be in are driving high, driving low, and high impedance. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10 kΩ resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

8.3.2 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Electrical Placement of Clamping Diodes for Each Input and Output](#).

注意

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

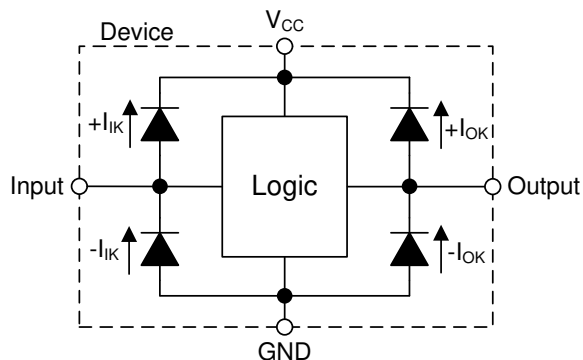


図 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

表 8-1. Function Table

INPUTS		OUTPUT
OE	A	Y
L	X	Z
H	L	L
H	H	H

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

In this application, a buffer with a 3-state output is used to disable a data signal as shown in [Figure 9-1](#). The remaining three buffers can be used for signal conditioning in other places in the system, or the inputs can be grounded and the channels left unused.

9.2 Typical Application

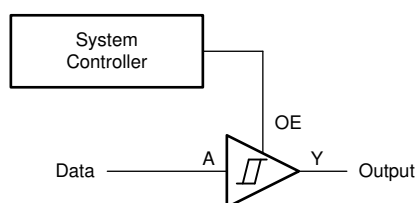


Figure 9-1. Typical application block diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS126 plus the maximum static supply current, I_{CC} , listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS126 plus the maximum supply current, I_{CC} , listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCS126 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HCS126 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

注意

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS126, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74HCS126 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS126 to the receiving device(s).
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

9.2.3 Application Curves

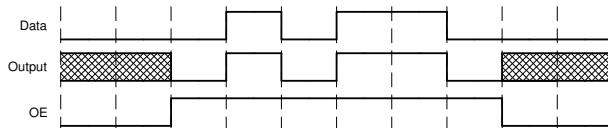


FIG 9-2. Application timing diagram

10 Power Supply Recommendations

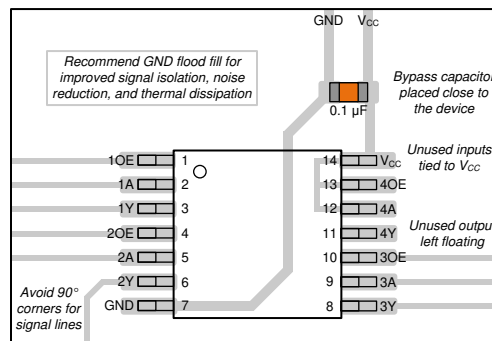
The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example



11-1. Example layout for the SN74HCS126-Q1

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [HCMOS Design Considerations application report](#) (SCLA007)
- Texas Instruments, [CMOS Power Consumption and \$C_{pd}\$ Calculation application report](#) (SDYA009)
- Texas Instruments, [Designing With Logic application report](#)

12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](#) のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.3 サポート・リソース

[TI E2E™ サポート・フォーラム](#)は、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

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12.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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12.5 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい ESD 対策をとらないと、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

12.6 用語集

[TI 用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74HCS126DR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HCS126
SN74HCS126DR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS126
SN74HCS126DYYR	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS126
SN74HCS126DYYR.A	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS126
SN74HCS126PWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HCS126
SN74HCS126PWR.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS126
SN74HCS126PWR.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	-	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS126

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74HCS126 :

- Automotive : [SN74HCS126-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

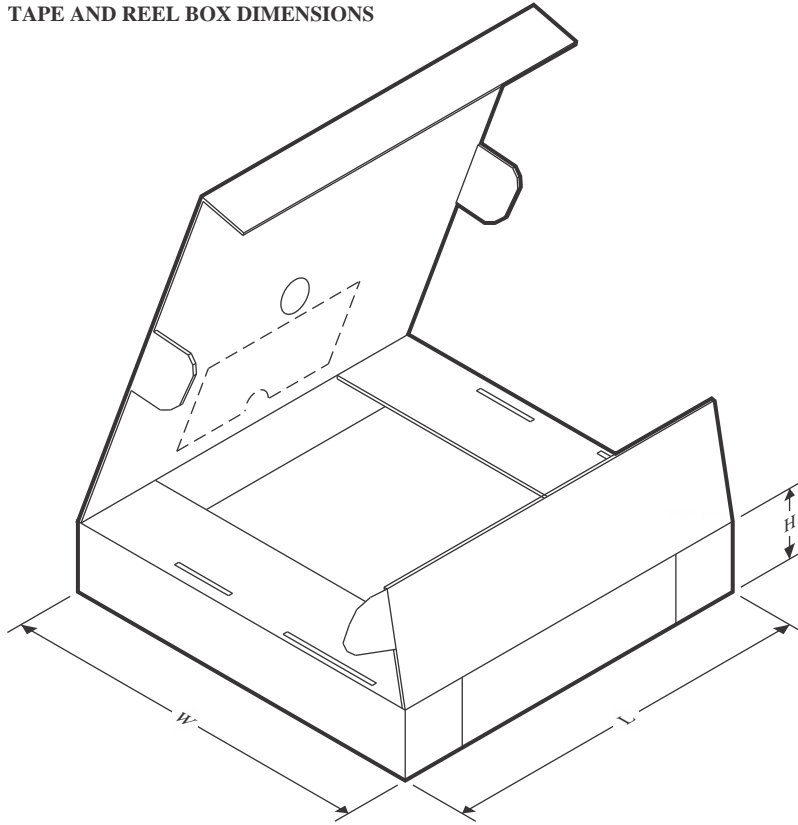
TAPE AND REEL INFORMATION



*All dimensions are nominal

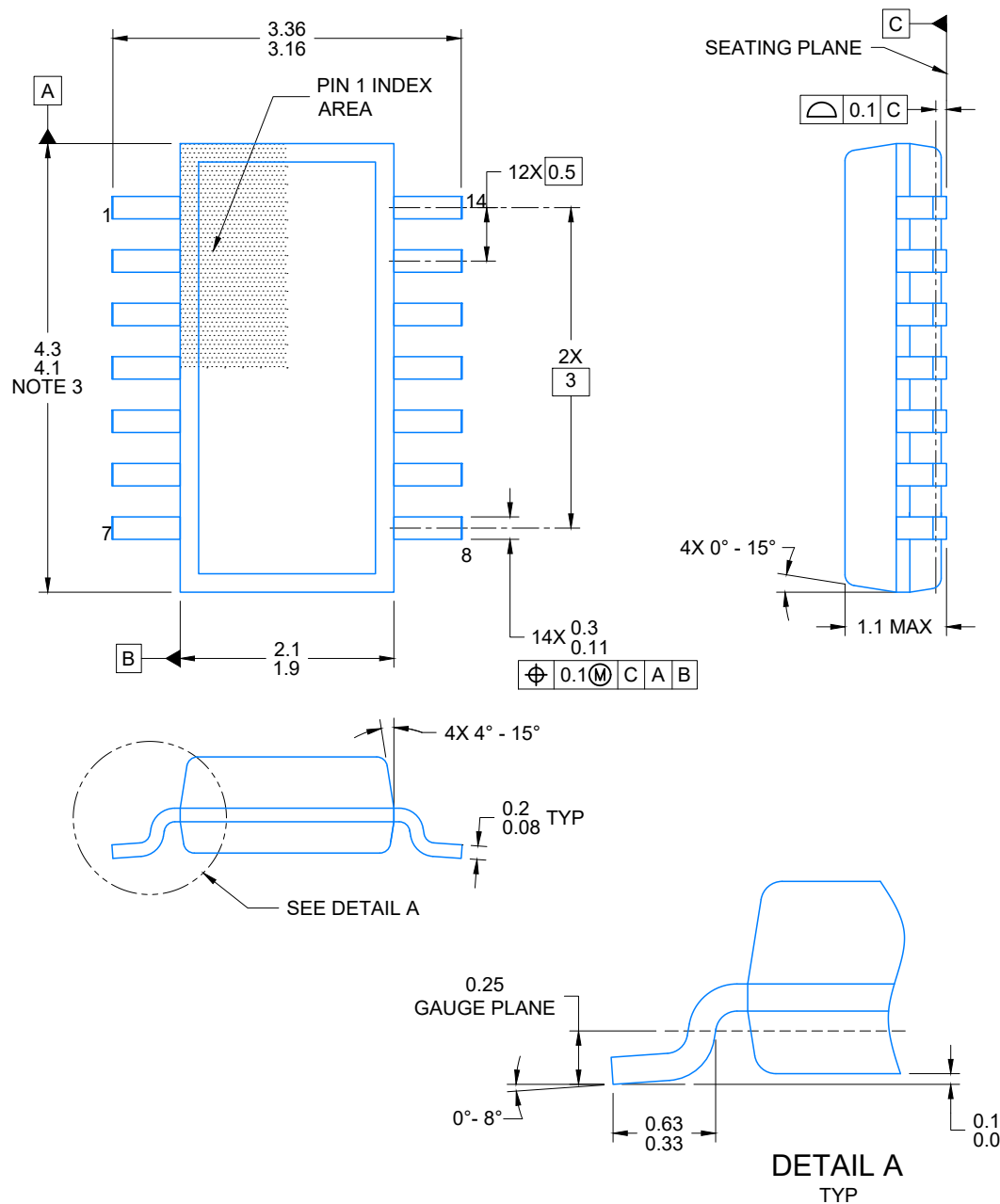
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS126DR	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HCS126DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HCS126DYYR	SOT-23-THIN	DYY	14	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
SN74HCS126PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

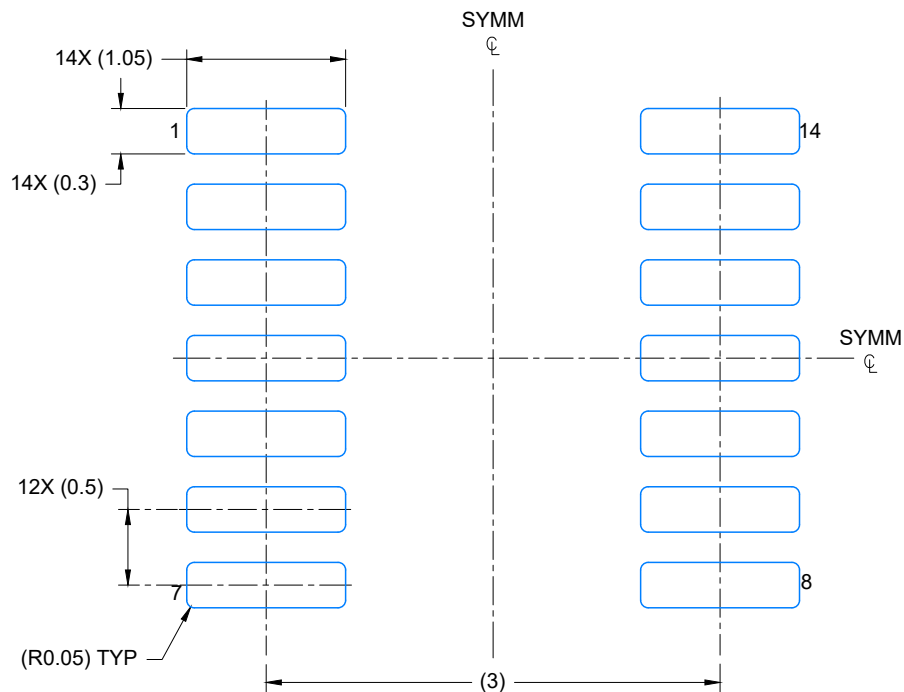
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS126DR	SOIC	D	14	2500	366.0	364.0	50.0
SN74HCS126DR	SOIC	D	14	2500	353.0	353.0	32.0
SN74HCS126DYYR	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8
SN74HCS126PWR	TSSOP	PW	14	2000	356.0	356.0	35.0



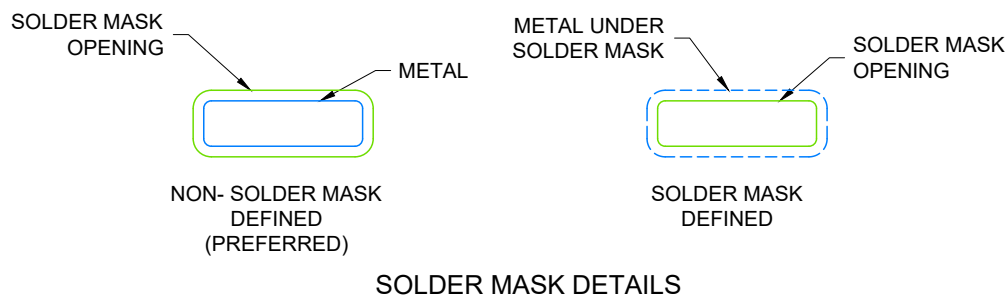
4224643/D 07/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AB



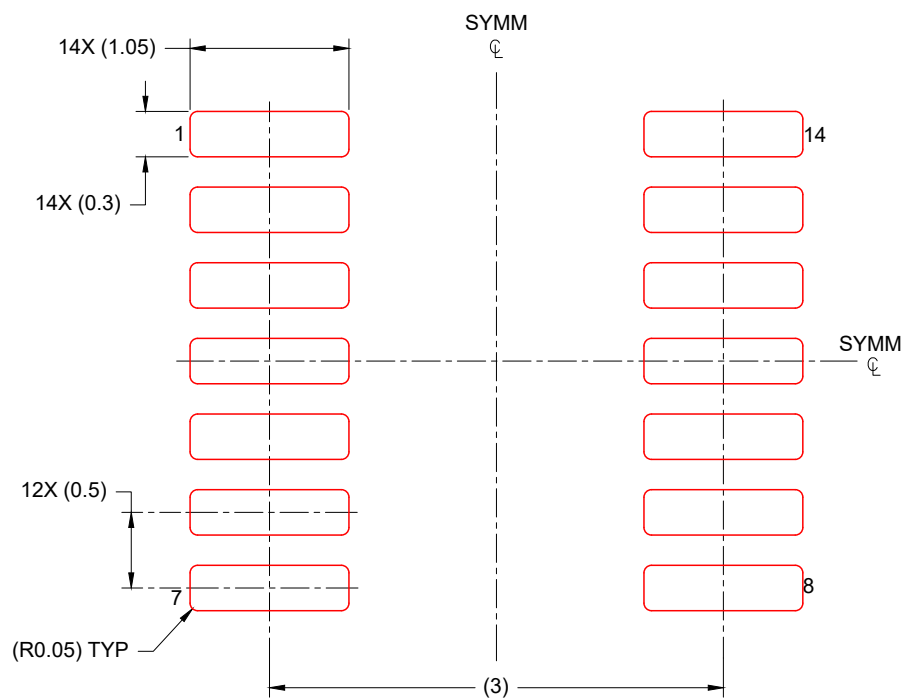
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224643/D 07/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

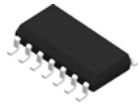


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 20X

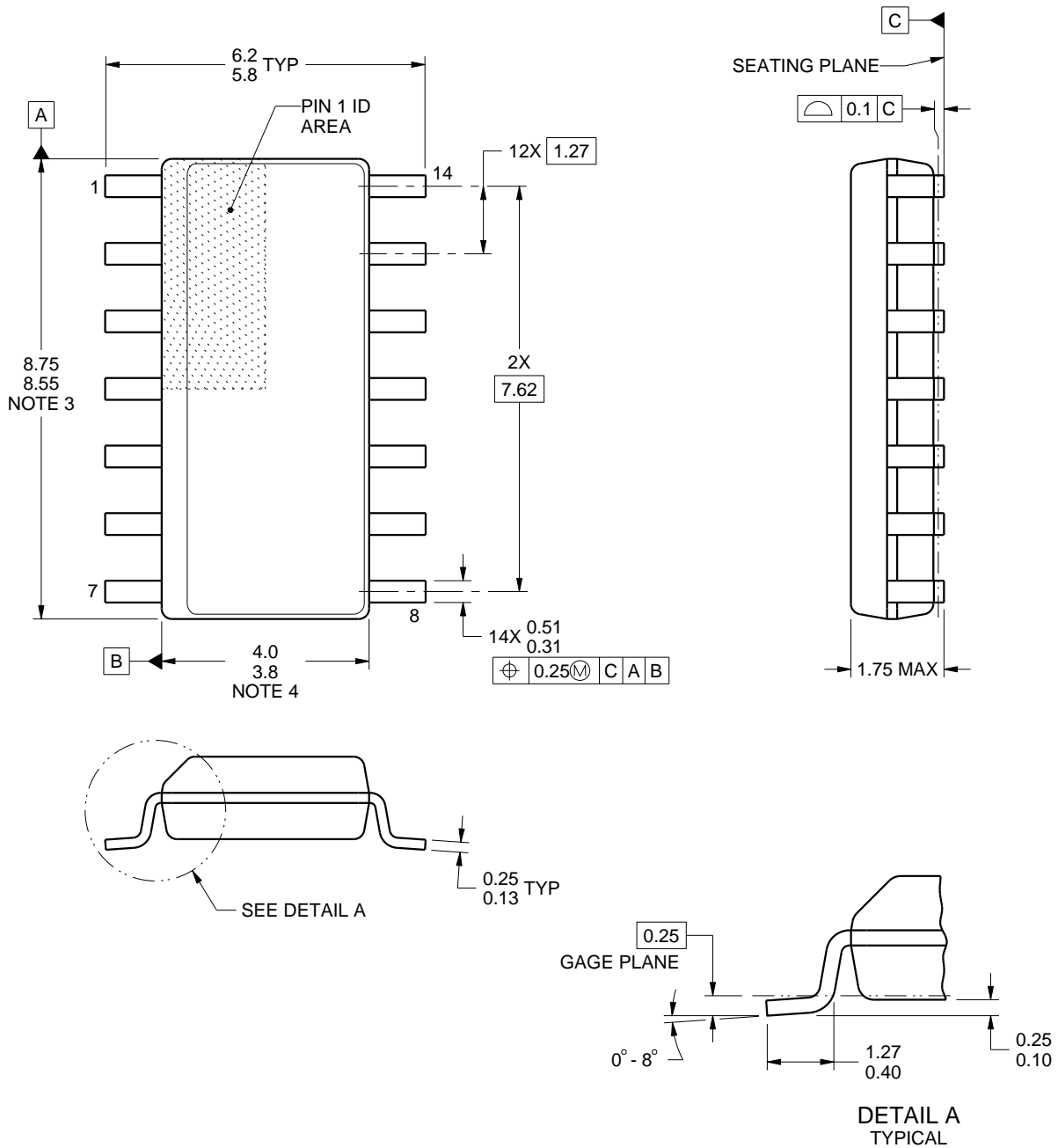
4224643/D 07/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

D0014A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

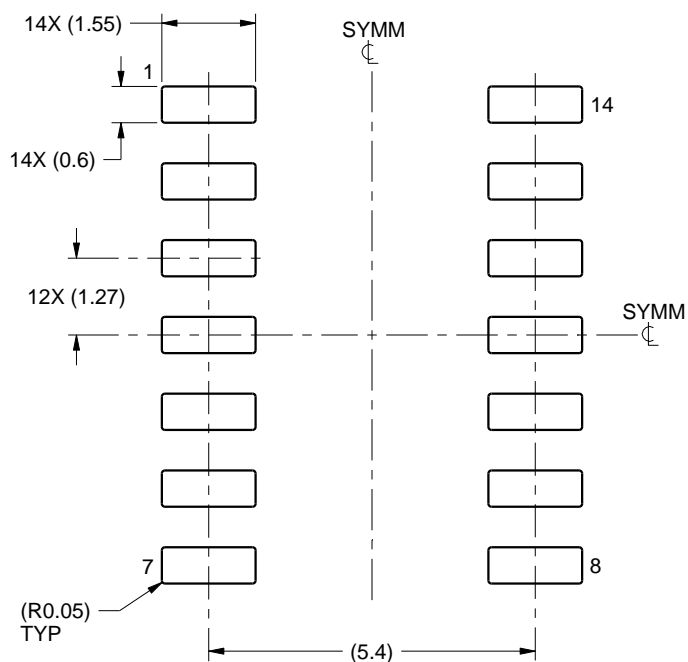
NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

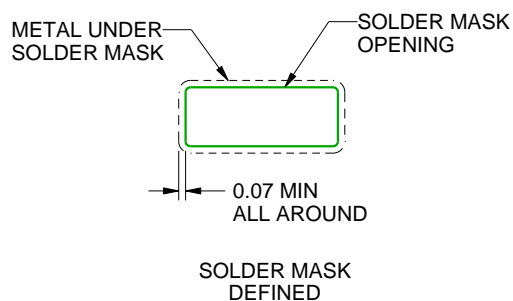
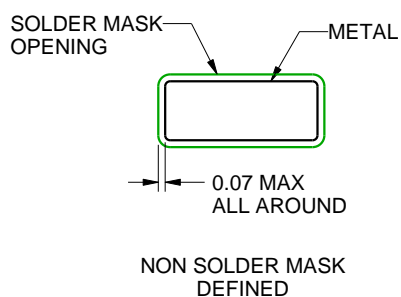
D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

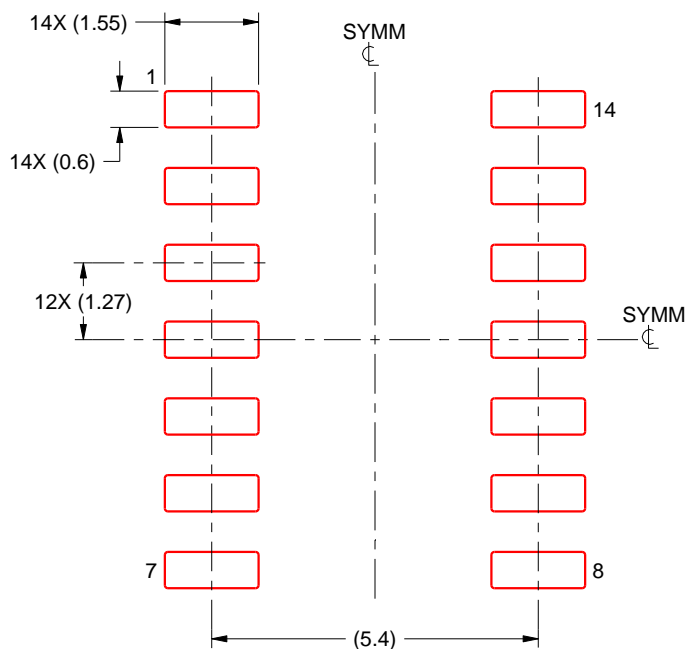
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

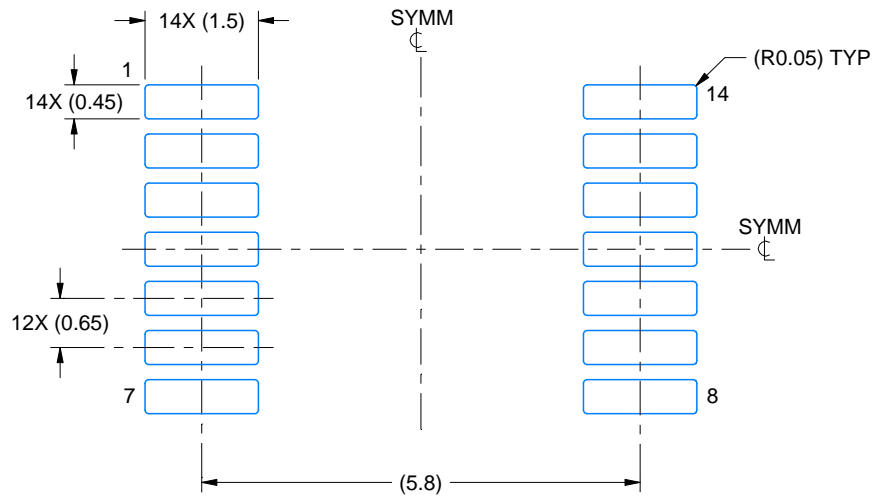
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

EXAMPLE BOARD LAYOUT

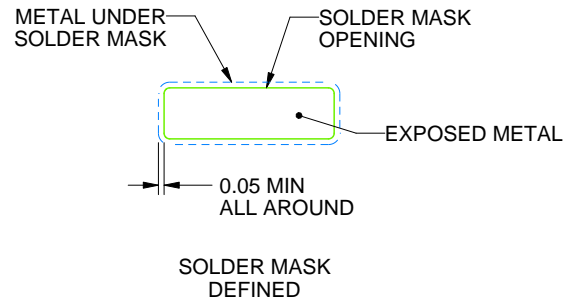
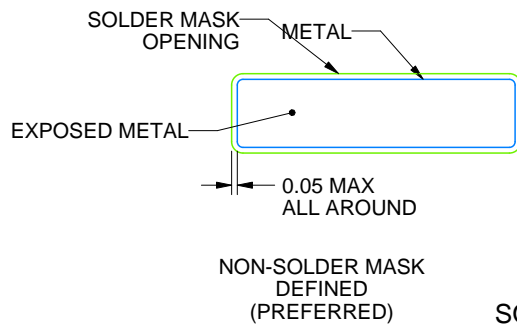
PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220202/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

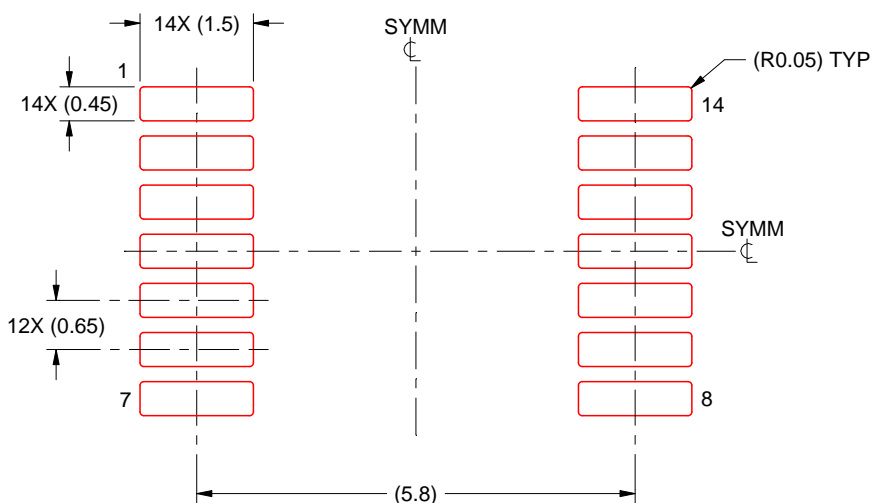
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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